

Amendments to the Claims

1-16. (Cancel)

17. (New) A low-reflective thin-film substrate comprising:

a thin film formed in multilayer on a transparent glass substrate by sputtering a target material containing no chromium component and comprising an alloy of at least one of Ni, Fe and Co and at least one of Mo, W, Ta and Nb,

wherein the low-reflective thin-film substrate has a minimum reflectivity which is 0.5% or lower and an optical density of at least 4 in the visible light region.

18. (New) The low-reflective thin-film substrate of claim 17, wherein the thin film is formed by sputtering under a gas atmosphere of at least one of an inert gas, an oxygen gas, and a carbon oxide gas in a vacuum film-forming apparatus.

19. (New) The low-reflective thin-film substrate of claim 17, wherein the target material contains at least one of Cu, Ti, Zr and Sn.

20. (New) The low-reflective thin-film substrate of claim 18, wherein the target material contains at least one of Cu, Ti, Zr and Sn.

21. (New) A low-reflective thin-film substrate comprising:

a thin film formed in multilayer on a transparent glass substrate by sputtering a target material containing no chromium component and comprising an alloy of at least two of Ni, Fe and Co,

wherein the low-reflective thin-film substrate has a minimum reflectivity which is 0.5% or lower and an optical density of at least 4 in the visible light region.

22. (New) The low-reflective thin-film substrate of claim 21, wherein the thin film is formed by sputtering under a gas atmosphere of at least one of an inert gas, an oxygen gas, and a carbon oxide gas in a vacuum film-forming apparatus.

23. (New) The low-reflective thin-film substrate of claim 21, wherein the target material contains at least one of Cu, Ti, Zr and Sn.

24. (New) The low-reflective thin-film substrate of claim 22, wherein the target material contains at least one of Cu, Ti, Zr and Sn.